TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

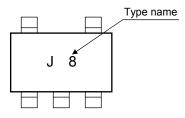
# TC7SZ86F,TC7SZ86FU

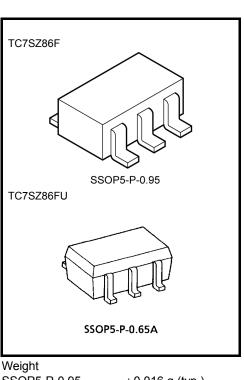
#### EXCLUSIVE OR Gate

#### Features

- High output drive: ±24 mA (min) at V<sub>CC</sub> = 3 V
- Super high speed operation: t<sub>pd</sub>=2.9 ns (typ.)
  - at V<sub>CC</sub> = 5 V, 50 pF
- Operation voltage range: V<sub>CC (opr)</sub> = 1.8~5.5 V
- 5.5-V tolerant inputs
- 5.5-V power down protection output
- Matches the performance of TC74LCX series when operated at 3.3- V  $V_{CC}$

#### Marking





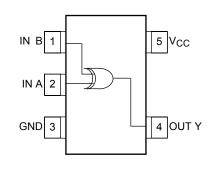
SSOP5-P-0.95 SSOP5-P-0.65A

#### : 0.016 g (typ.) : 0.006 g (typ.)

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	-0.5~6	V
DC input voltage	V <sub>IN</sub>	-0.5~6	V
DC output voltage	V <sub>OUT</sub>	-0.5~6	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	IOK	-20	mA
DC output current	IOUT	±50	mA
DC V <sub>CC</sub> /ground current	ICC	±50	mA
Power dissipation	PD	200	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C
Lead temperature (10s)	ΤL	260	°C

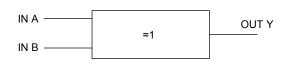
#### Pin Assignment (top view)



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Logic Diagram



### Truth Table

Inp	out	Output
А	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

### **Operating Ranges**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	1.8~5.5	V	
Supply voltage		1.5~5.5 (Note 1)	v	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~5.5 (Note 2)	V	
		0~V <sub>CC</sub> (Note 3)	v	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
	dt/dv	0~20 (V_{CC} = 1.8 V, 2.5 V $\pm$ 0.2 V)	ns/V	
Input rise and fall time		0~10 (V_{CC} = 3.3 V $\pm$ 0.3 V)		
		0~5 (V <sub>CC</sub> = 5.5 V $\pm$ 0.5 V)		

Note 1: Data retention only

Note 2: V<sub>CC</sub> = 0 V

Note 3: High or Low state

### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol Test Cond		at Condition	Condition		Ta = 25°C			Ta = -40~85°C		
		V <sub>CC</sub> (V)		Min	Тур.	Max	Min	Max	Unit	
High-level input		1.8		0.75 × V <sub>CC</sub>	_	_	$0.75 \times V_{CC}$	_	V	
voltage VIH				$0.7 \times V_{CC}$		_	$0.7 \times V_{CC}$	_	v	
Low-level input VIL VIL			1.8	_		$0.25 \times V_{CC}$	_	$0.25 \times V_{CC}$	V	
		—	2.3-5.5	_		$0.3 \\ \times V_{CC}$	_	$0.3 \\ \times V_{CC}$	V	
				1.8	1.7	1.8	—	1.7	—	
			I <sub>OH</sub> = –100 μA	2.3	2.2	2.3	—	2.2	_	
			$10H = -100 \ \mu A$	3.0	2.9	3.0	—	2.9	_	
High-level	Vон	$V_{IN} = V_{IH}$		4.5	4.4	4.5	—	4.4	_	V
output voltage	∨ОН	or V <sub>IL</sub>	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.15	_	1.9	_	V
			I <sub>OH</sub> = -16 mA	3.0	2.4	2.8	—	2.4	_	
		I <sub>OH</sub> = -24 mA	3.0	2.3	2.68	—	2.3	_		
			I <sub>OH</sub> = -32 mA	4.5	3.8	4.2	—	3.8	_	
			I <sub>OL</sub> = 100 μA	1.8	_	0	0.1	—	0.1	- V
				2.3	_	0	0.1	—	0.1	
				3.0	_	0	0.1	—	0.1	
Low-level	V <sub>OL</sub>	$V_{IN} = V_{IH}$		4.5	_	0	0.1	—	0.1	
output voltage	VOL	or V <sub>IL</sub>	I <sub>OL</sub> = 8 mA	2.3	_	0.1	0.3	_	0.3	
		I <sub>OL</sub> = 16 mA	3.0	_	0.15	0.4	_	— 0.4		
		I <sub>OL</sub> = 24 mA	l <sub>OL</sub> = 24 mA 3.0 —	0.22	0.55	_	0.55			
			I <sub>OL</sub> = 32 mA	4.5	_	0.22	0.55	_	0.55	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V	V <sub>IN</sub> = 5.5 V or GND		_		±1	_	±10	μA
Power off leakage current	IOFF	$V_{IN}$ or $V_{OUT} = 5.5 V$		0.0	_	_	1	_	10	μΑ
Quiescent supply current	Icc	$V_{IN} = V_{CC}$	$V_{IN} = V_{CC}$ or GND		_	_	2	_	20	μA

### AC Characteristics (unless otherwise specified, Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = −40~85°C		Unit	
Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time	<sup>t</sup> pLH tpHL	$C_L = 15 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	1.8	2.0	5.7	11.5	2.0	12.0	- ns
			$2.5\pm0.2$	0.8	3.8	8.0	0.8	8.5	
			$\textbf{3.3}\pm\textbf{0.3}$	0.5	3.0	5.7	0.5	6.0	
			$5.0\pm0.5$	0.5	2.4	5.0	0.5	5.4	
		$\begin{array}{l} C_{L} = 50 \; pF, \\ R_{L} = 500 \; \Omega \end{array}$	$\textbf{3.3}\pm\textbf{0.3}$	1.2	3.5	6.2	1.5	6.5	
			$5.0\pm0.5$	0.8	2.9	5.4	1.0	5.8	
Input capacitance	C <sub>IN</sub>		0~5.5	_	4	_	_	_	pF
Power dissipation capacitance	6	(Note 4)	3.3		21	_			pF
	C <sub>PD</sub>		5.5		24	_		_	

Note 4: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

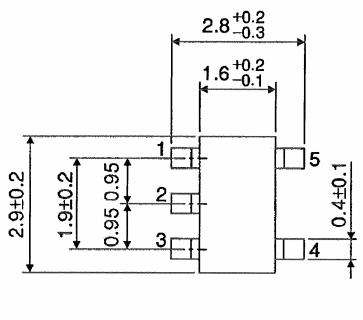
Average operating current can be obtained by the equation:

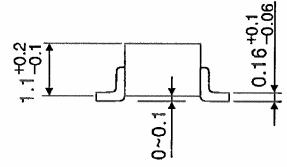
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

### Package Dimensions

SSOP5-P-0.95

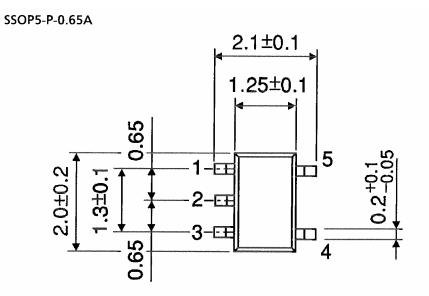
Unit : mm

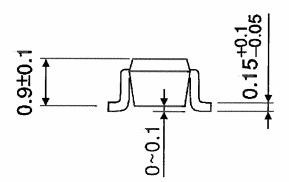




Weight: 0.016 g (typ.)

### Package Dimensions





Weight: 0.006 g (typ.)

Unit : mm

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20070701-EN GENERAL

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